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Kind regards,

Team Nexperia

PDTA114Y series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

Rev. 5 — 18 November 2011

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number				NPN	Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTA114YE	SOT416	SC-75	-	PDTC114YE	ultra small	
PDTA114YM	SOT883	SC-101	-	PDTC114YM	leadless ultra small	
PDTA114YT	SOT23	-	TO-236AB	PDTC114YT	small	
PDTA114YU	SOT323	SC-70	-	PDTC114YU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital applications in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		3.7	4.7	5.7	



2. Pinning information

Table 3. **Pinning** Simplified outline **Graphic symbol** Pin Description SOT23; SOT323; SOT416 1 input (base) 3 2 GND (emitter) 3 output (collector) 2 006aaa144 sym003 **SOT883** 1 input (base) 2 GND (emitter) output (collector) Transparent top view

3. Ordering information

Table 4. Ordering information

Type number	Package	Package						
	Name	Description	Version					
PDTA114YE	SC-75	plastic surface-mounted package; 3 leads	SOT416					
PDTA114YM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883					
PDTA114YT	-	plastic surface-mounted package; 3 leads	SOT23					
PDTA114YU	SC-70	plastic surface-mounted package; 3 leads	SOT323					

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTA114YE	36
PDTA114YM	DF
PDTA114YT	*29
PDTA114YU	*55

[1] * = placeholder for manufacturing site code

sym003

5. Limiting values

Table 6. Limiting values

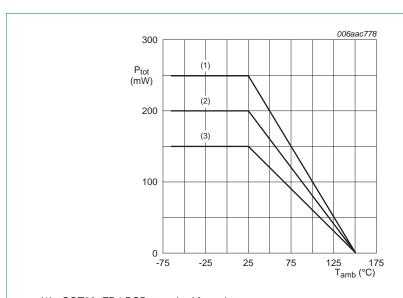
In accordance with the Absolute Maximum Rating System (IEC 60134).

			<u> </u>		
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
V_{I}	input voltage				
	positive		-	+6	V
	negative		-	-40	V
Io	output current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTA114YE (SOT416)		[1][2]	150	mW
	PDTA114YM (SOT883)		[2][3]	250	mW
	PDTA114YT (SOT23)		<u>[1]</u> -	250	mW
	PDTA114YU (SOT323)		<u>[1]</u> -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTA114YE (SOT416)		[1][2]	-	830	K/W
	PDTA114YM (SOT883)		[2][3]	-	500	K/W
	PDTA114YT (SOT23)		[1] -	-	500	K/W
	PDTA114YU (SOT323)		<u>[1]</u> _	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.

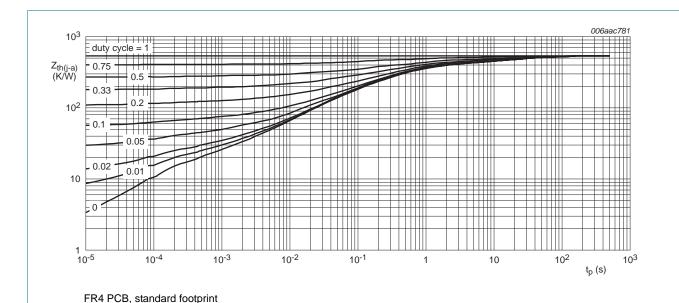


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114YE (SOT416); typical values

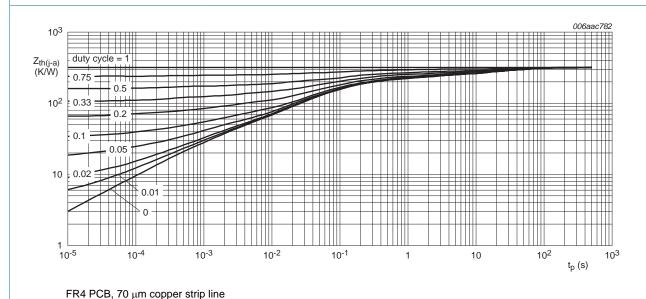


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114YM (SOT883); typical values

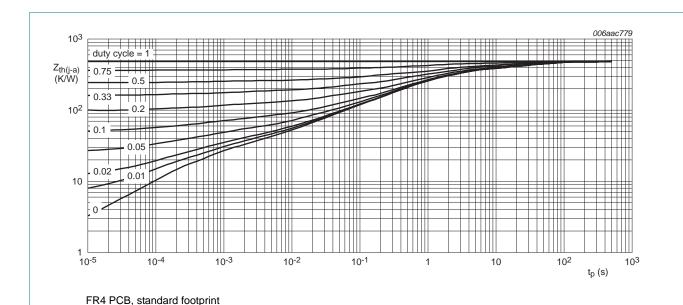


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114YT (SOT23); typical values

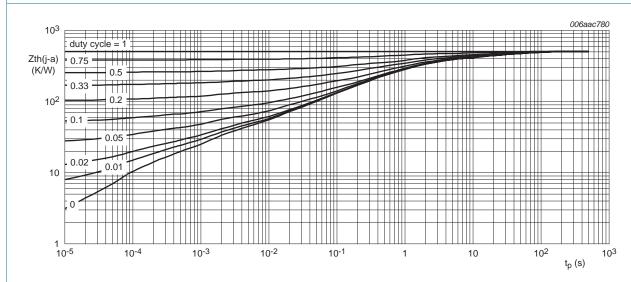


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114YU (SOT323); typical values

FR4 PCB, standard footprint

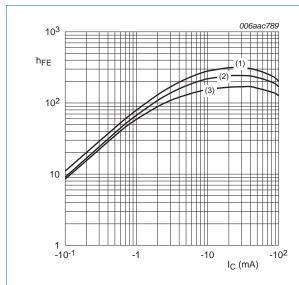
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	-1	μΑ
	cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-150	μА
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	100	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	-	-	-100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-0.7	-0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -1 \text{ mA}$	-1.4	-0.8	-	V
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		3.7	4.7	5.7	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; $ [1] $f = 100 \text{ MHz}$	-	180	-	MHz

[1] Characteristics of built-in transistor



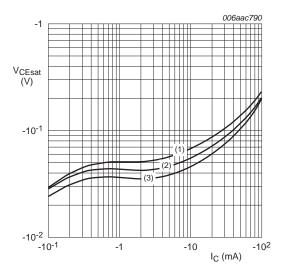


(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 6. DC current gain as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

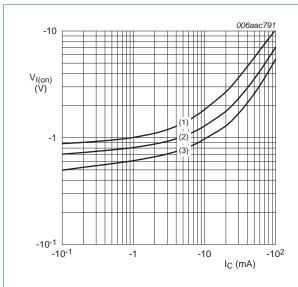
(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

PDTA114Y_SER

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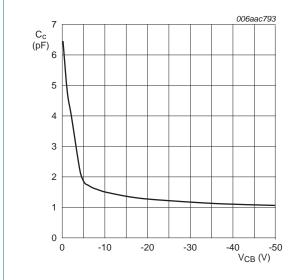


$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

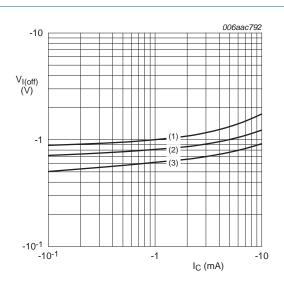
(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Fig 8. On-state input voltage as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 10. Collector capacitance as a function of collector-base voltage; typical values



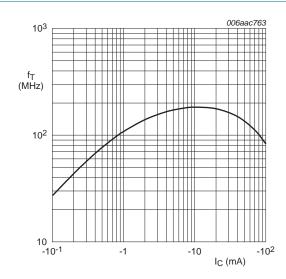
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 9. Off-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$$

Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

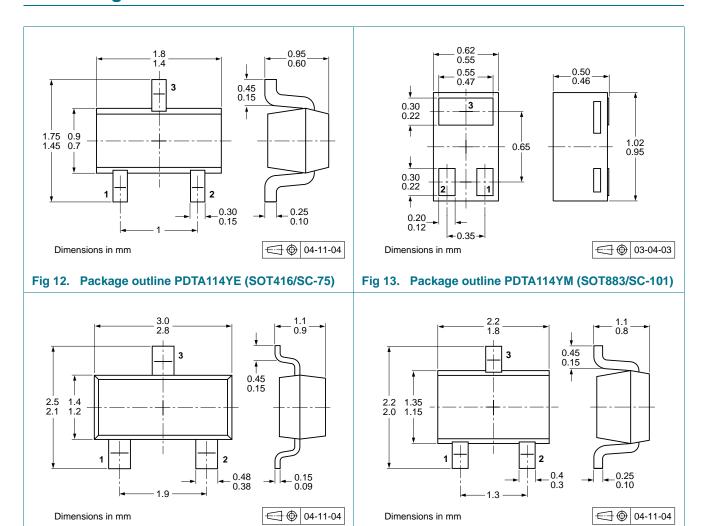


Fig 15. Package outline PDTA114YU (SOT323/SC-70)

Fig 14. Package outline PDTA114YT (SOT23)

10. Packing information

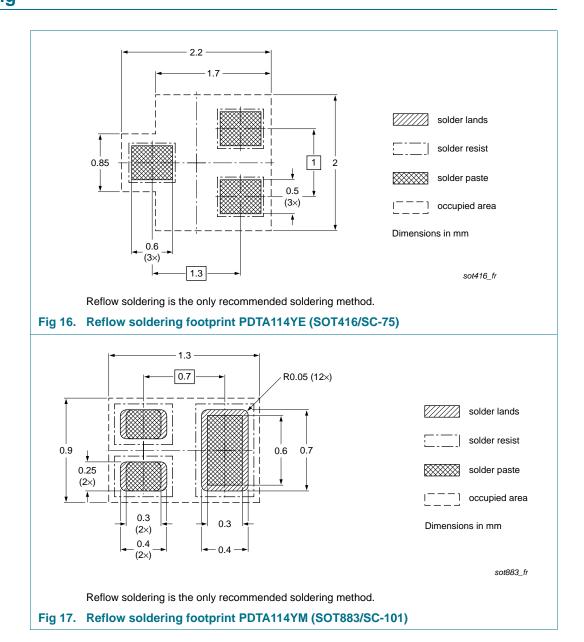
Table 9. Packing methods

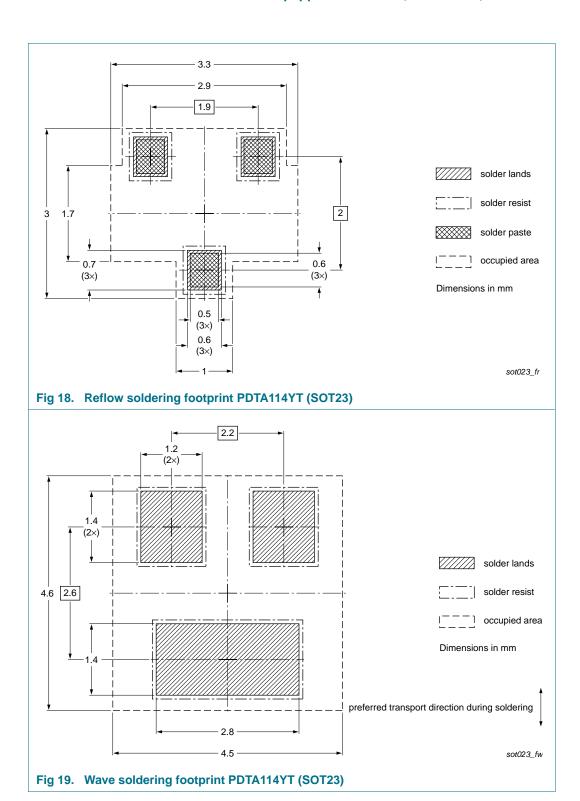
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

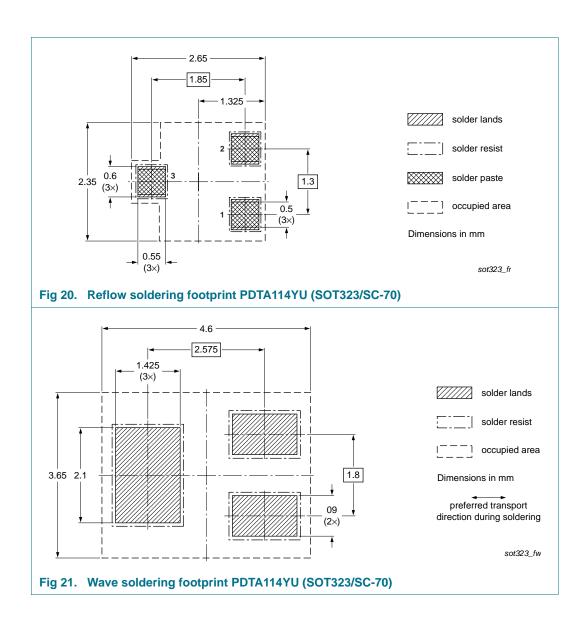
Type number	Package	Description	Packing	Packing quantity			
			3000	5000	10000		
PDTA114YE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135		
PDTA114YM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315		
PDTA114YT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235		
PDTA114YU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135		

^[1] For further information and the availability of packing methods, see <u>Section 14</u>.

11. Soldering







12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PDTA114Y_SER v.5	20111118	Product data sheet	-	PDTA114Y_SERIES v.4			
Modifications:		f this document has been red NXP Semiconductors.	esigned to comply wi	th the new identity			
	 Legal texts have been adapted to the new company name where appropriate. 						
	 Type numbers PDTA114YEF, PDTA114YK and PDTA114YS removed. 						
	Section 1 "Product profile": updated						
	 Section 3 "Ordering information": added 						
	 Section 4 "Marking": updated 						
	• Figure 1 to 11: added						
	Section 5 "Limiting values": updated						
	 Section 6 "Thermal characteristics": updated 						
	 <u>Table 8 "Characteristics"</u>: V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated, f_T added 						
	Section 8 "Test information": added						
	 Section 9 "Package outline": superseded by minimized package outline drawings 						
	Section 10 "Packing information": added						
	Section 11 "Soldering": added						
	 Section 13 "L 	egal information": updated					
PDTA114Y_SERIES v.4	20040802	Product data sheet	-	PDTA114Y_SERIES v.3			
PDTA114Y_SERIES v.3	20030909	Product specification	-	PDTA114Y_SERIES v.2			
PDTA114Y_SERIES v.2	20030411	Product specification	-	PDTA114YEF v.1			
PDTA114YEF v.1	20020515	Product specification	-	-			

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTA114Y series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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PDTA114Y series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

15. Contents

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